TS882

Rail-to-rail 1.1 V dual nanopower comparator

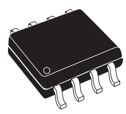
Datasheet - production data

Features

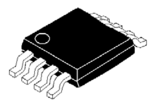
- Ultra low current consumption: 220 nA typ./op.
- Propagation delay: 2 µs typ.
- Rail-to-rail inputs
- Push-pull outputs
- Supply operation from 1.1 V to 5.5 V
- Wide temperature range: -40 to +125 °C
- ESD tolerance: 6 kV HBM / 300 V MM
- Available in SO8, MiniSO8, and DFN8 2 x 2 mm package

Related product

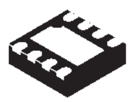
- See the TS881 datasheet for single operator with smaller package.



SO8



MiniSO8



DFN8 2 x 2 mm

Applications

- Portable systems
- Signal conditioning
- Medical

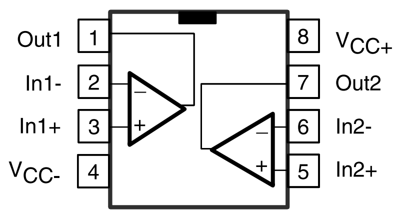
Description

The TS882 device is a dual comparator featuring ultra low supply current (220 nA typical per operator with output high, V_{CC} = 1.2 V, no load) with rail-to-rail input and output capability. The performance of this comparator allows it to be used in a wide range of portable applications. The TS882 device minimizes battery supply leakage and therefore enhances battery lifetime.

Operating from 1.1 to 5.5 V supply voltage, this comparator can be used over a wide temperature range (-40 to +125 °C) keeping the current consumption at an ultra low level.

The TS882 device is available in the SO8, MiniSO8 and DFN8 2 x 2 mm packages, allowing great space saving on the PCB.

Figure 1. Pin connections (top view)



TS882IDT/IST/IQ2T
SO8/MiniSO8/DFN8

This is information on a product in full production. www.st.com

Contents

1 Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage(1)	6	V
V_{ID}	Differential input voltage(2)	±6	V
V_{IN}	Input voltage range	$(V_{CC}\text{-})$ - 0.3 to $(V_{CC}\text{+})$ + 0.3	V
R_{THJA}	Thermal resistance junction-to-ambient(3) SO8 MiniSO8 DFN8 2 x 2 mm	 125 190 57	°C/W
T_{STG}	Storage temperature	-65 to +150	°C
T_J	Junction temperature	150	°C
T_{LEAD}	Lead temperature (soldering 10 seconds)	260	°C
ESD	Human body model (HBM)(4)	6	kV
	Machine model (MM)(5)	300	V
	Charged device model (CDM)(6)	1300	
	Latch-up immunity	200	mA

1. All voltage values, except differential voltages, are referenced to V_{CC}-. V_{CC} is defined as the difference between V_{CC}+ and V_{CC}-.
2. The magnitude of input and output voltages must never exceed the supply rail ±0.3 V.
3. Short-circuits can cause excessive heating. These values are typical.
4. According to JEDEC standard JESD22-A114F.
5. According to JEDEC standard JESD22-A115A.
6. According to ANSI/ESD STM5.3.1.

Table 2. Operating conditions

Symbol	Parameter	Value	Unit
T_{oper}	Operating temperature range	-40 to +125	°C
V_{CC}	Supply voltage -40 °C < T_{amb} < +125 °C	1.1 to 5.5	V
V_{ICM}	Common mode input voltage range -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C	 (V_{CC-}) - 0.2 to (V_{CC+}) + 0.2 (V_{CC-}) to (V_{CC+}) + 0.2	V

2 Electrical characteristics

Table 3. V_{CC} = +1.2 V, T_{amb} = +25 °C, V_{ICM} = $V_{CC}/2$ (unless otherwise specified)(1)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IO}	Input offset voltage(2)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C	 -6	1	 6	mV
ΔV_{IO}	Input offset voltage drift	-40 °C < T_{amb} < +125 °C		3		µV/°C
V_{HYST}	Input hysteresis voltage(3)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C	 1.5	2.4	 4.2	mV
I_{IO}	Input offset current(4)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C			10 100	pA
I_{IB}	Input bias current(4)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C		1	10 100	pA
I_{CC}	Supply current per operator	No load, output low, V_{ID} = -0.1 V -40 °C < T_{amb} < +125 °C No load, output high, V_{ID} = +0.1 V -40 °C < T_{amb} < +125 °C		300 220 	 450 350	nA
I_{SC}	Short-circuit current	Source Sink		1.0 1.7		mA
V_{OH}	Output voltage high	I_{source} = 0.2 mA -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C	1.13 1.10 1.00	1.15		V
V_{OL}	Output voltage low	I_{sink} = 0.2 mA -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C		35	50 60 70	mV
CMRR	Common mode rejection ratio	0 < V_{ICM} < V_{CC} -40 °C < T_{amb} < +125 °C	 50	68		dB
T_{PLH}	Propagation delay (low to high)	f = 1 kHz, C_L = 30 pF, R_L = 1 MΩ Overdrive = 10 mV -40 °C < T_{amb} < +125 °C Overdrive = 100 mV -40 °C < T_{amb} < +125 °C		 5.5 2.1 	 11 13 3.1 3.4	µs
T_{PHL}	Propagation delay (high to low)	f = 1 kHz, C_L = 30 pF, R_L = 1 MΩ Overdrive = 10 mV -40 °C < T_{amb} < +125 °C Overdrive = 100 mV -40 °C < T_{amb} < +125 °C		 5.1 1.9 	 8 10 2.6 3.1	µs
T_R	Rise time (10% to 90%)	C_L = 30 pF, R_L = 1 MΩ		100		ns

Table 3. V_{CC} = +1.2 V, T_{amb} = +25 °C, V_{ICM} = $V_{CC}/2$ (unless otherwise specified)(1) (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
T_F	Fall time (90% to 10%)	C_L = 30 pF, R_L = 1 MΩ		110		ns
T_{ON}	Power-up time			1.1	1.7	ms

1. All values over the temperature range are guaranteed through correlation and simulation. No production test is performed at the temperature range limits.
2. The offset is defined as the average value of positive and negative trip points (input voltage differences requested to change the output state in each direction).
3. The hysteresis is a built-in feature of the TS882 device. It is defined as the voltage difference between the trip points.
4. Maximum values include unavoidable inaccuracies of the industrial tests.

Table 4. V_{CC} = +2.7 V, T_{amb} = +25 °C, V_{ICM} = V_{CC}/2 (unless otherwise specified)(1)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IO}	Input offset voltage(2)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C	 -6	1	 6	mV
ΔV_{IO}	Input offset voltage drift	-40 °C < T_{amb} < +125 °C		3		µV/°C
V_{HYST}	Input hysteresis voltage(3)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C	 1.6	2.7	 4.2	mV
I_{IO}	Input offset current(4)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C			10 100	pA
I_{IB}	Input bias current(4)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C		1	10 100	pA
I_{CC}	Supply current per operator	No load, output low, V_{ID} = -0.1 V -40 °C < T_{amb} < +125 °C No load, output high, V_{ID} = +0.1 V -40 °C < T_{amb} < +125 °C		310 220	 450 350	nA
I_{SC}	Short-circuit current	Source Sink		10 13		mA
V_{OH}	Output voltage high	I_{source} = 2 mA -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C	2.48 2.40 2.10	2.51		V
V_{OL}	Output voltage low	I_{sink} = 2 mA -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C		130	210 230 310	mV
CMRR	Common mode rejection ratio	0 < V_{ICM} < V_{CC} -40 °C < T_{amb} < +125 °C	 55	74		dB
T_{PLH}	Propagation delay (low to high)	f = 1 kHz, C_L = 30 pF, R_L = 1 MΩ Overdrive = 10 mV -40 °C < T_{amb} < +125 °C Overdrive = 100 mV -40 °C < T_{amb} < +125 °C		 6.4 2.3	 12 14 3.0 3.7	µs
T_{PHL}	Propagation delay (high to low)	f = 1 kHz, C_L = 30 pF, R_L = 1 MΩ Overdrive = 10 mV -40 °C < T_{amb} < +125 °C Overdrive = 100 mV -40 °C < T_{amb} < +125 °C		 6.4 2.2	 12 14 3.0 3.7	µs
T_R	Rise time (10% to 90%)	C_L = 30 pF, R_L = 1 MΩ		120		ns
T_F	Fall time (90% to 10%)	C_L = 30 pF, R_L = 1 MΩ		130		ns
T_{ON}	Power-up time			1.1	1.7	ms

1. All values over the temperature range are guaranteed through correlation and simulation. No production test is performed at the temperature range limits.
2. The offset is defined as the average value of positive and negative trip points (input voltage differences requested to change the output state in each direction).
3. The hysteresis is a built-in feature of the TS882. It is defined as the voltage difference between the trip points.
4. Maximum values include unavoidable inaccuracies of the industrial tests.

Table 5. V_{CC} = +5 V, T_{amb} = +25 °C, V_{ICM} = V_{CC}/2 (unless otherwise specified)(1)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IO}	Input offset voltage(2)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C	 -6	1	 6	mV
ΔV_{IO}	Input offset voltage drift	-40 °C < T_{amb} < +125 °C		3		μV/°C
V_{HYST}	Input hysteresis voltage(3)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C	 1.6	3.1	 4.2	mV
I_{IO}	Input offset current(4)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C			10 100	pA
I_{IB}	Input bias current(4)	T_{amb} = +25 °C -40 °C < T_{amb} < +125 °C		1	10 100	pA
I_{CC}	Supply current per operator	No load, output low, V_{ID} = -0.1 V -40 °C < T_{amb} < +125 °C No load, output high, V_{ID} = +0.1 V -40 °C < T_{amb} < +125 °C		350 250 	 500 400	nA
I_{SC}	Short-circuit current	Source Sink		32 32		mA
V_{OH}	Output voltage high	I_{source} = 2 mA -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C	4.86 4.75 4.60	4.88		V
V_{OL}	Output voltage low	I_{sink} = 2 mA -40 °C < T_{amb} < +85 °C -40 °C < T_{amb} < +125 °C		90	130 170 280	mV
CMRR	Common mode rejection ratio	0 < V_{ICM} < V_{CC} -40 °C < T_{amb} < +125 °C	 55	78		dB
SVR	Supply voltage rejection	ΔV_{CC} = 1.2 V to 5 V -40 °C < T_{amb} < +125 °C	 65	80		dB
T_{PLH}	Propagation delay (low to high)	f = 1 kHz, C_L = 30 pF, R_L = 1 MΩ Overdrive = 10 mV -40 °C < T_{amb} < +125 °C Overdrive = 100 mV -40 °C < T_{amb} < +125 °C		 8.3 2.5 	 13 22 3.4 4.1	μs
T_{PHL}	Propagation delay (high to low)	f = 1 kHz, C_L = 30 pF, R_L = 1 MΩ Overdrive = 10 mV -40 °C < T_{amb} < +125 °C Overdrive = 100 mV -40 °C < T_{amb} < +125 °C		 9.0 2.6 	 16 19 3.5 4.2	μs
T_R	Rise time (10% to 90%)	C_L = 30 pF, R_L = 1 MΩ		160		ns

Table 5. V_{CC} = +5 V, T_{amb} = +25 °C, V_{ICM} = $V_{CC}/2$ (unless otherwise specified)(1) (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
T_F	Fall time (90% to 10%)	C_L = 30 pF, R_L = 1 MΩ		150		ns
T_{ON}	Power-up time			1.1	1.7	ms

1. All values over the temperature range are guaranteed through correlation and simulation. No production test is performed at the temperature range limits.
2. The offset is defined as the average value of positive and negative trip points (input voltage differences requested to change the output state in each direction).
3. The hysteresis is a built-in feature of the TS882 device. It is defined as the voltage difference between the trip points.
4. Maximum values include unavoidable inaccuracies of the industrial tests.

Figure 2. Current consumption per operator vs. supply voltage - output low

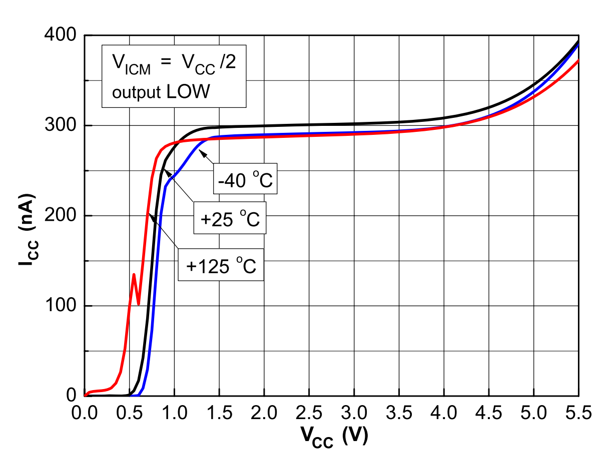


Figure 3. Current consumption per operator vs. supply voltage - output high

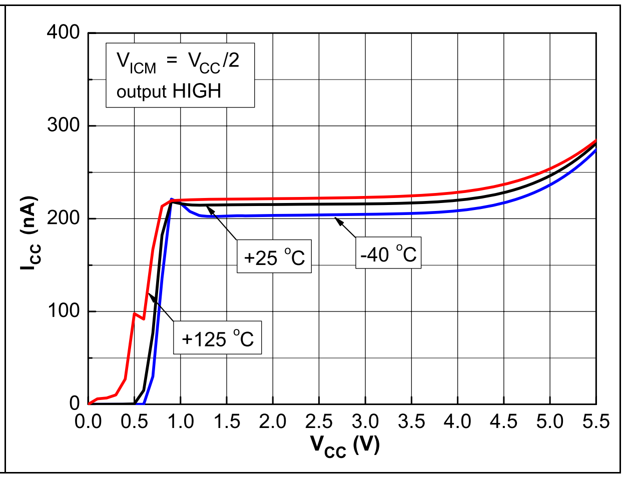


Figure 4. Current consumption per operator vs. input common mode voltage at V_{CC} = 1.2 V

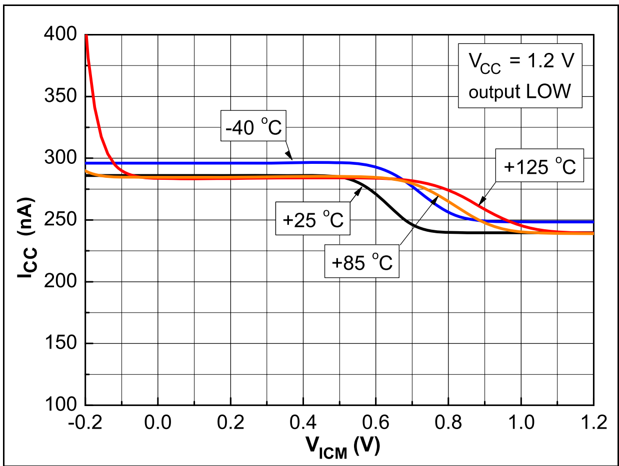


Figure 5. Current consumption per operator vs. input common mode voltage at V_{CC} = 5 V

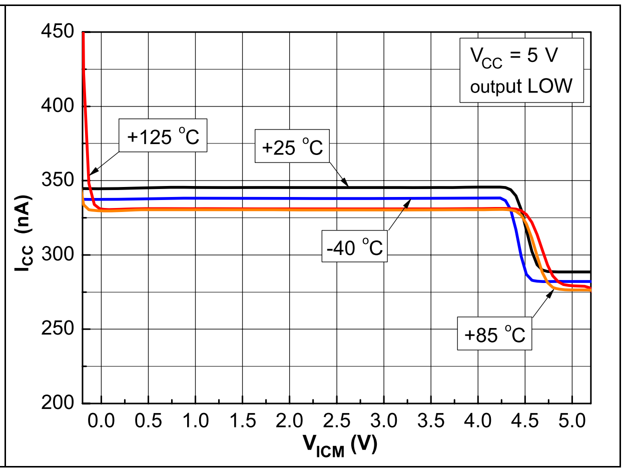


Figure 6. Current consumption per operator vs. temperature

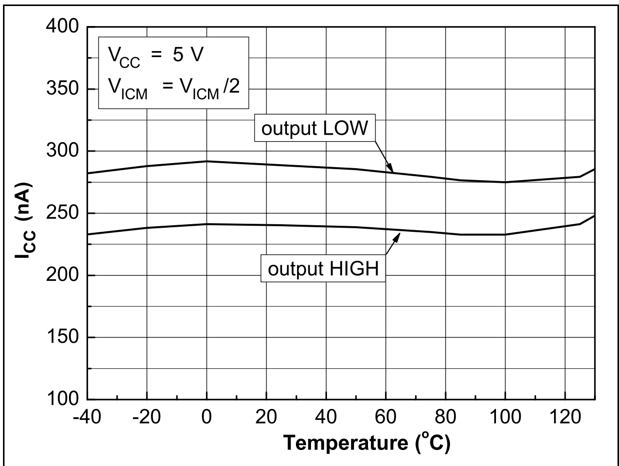


Figure 7. Current consumption per operator vs. toggle frequency

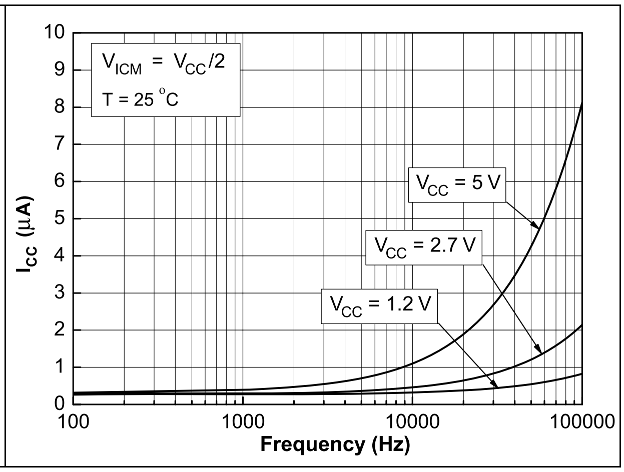


Figure 8. Input offset voltage vs. input common mode voltage at V_{CC} = 1.2 V

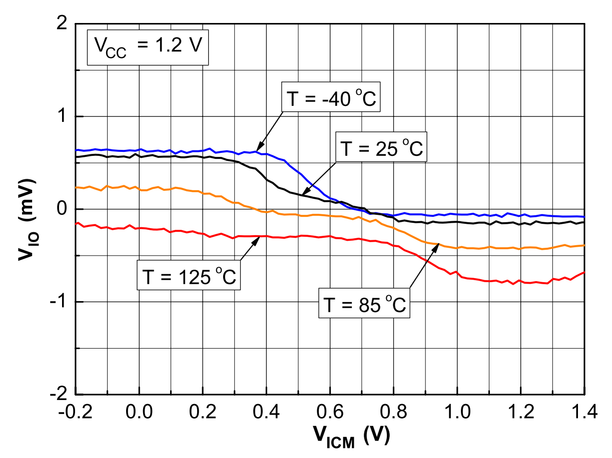


Figure 9. Input hysteresis voltage vs. input common mode voltage at V_{CC} = 1.2 V

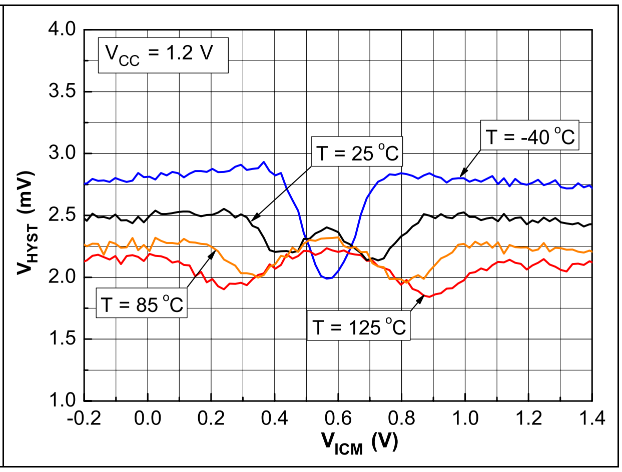


Figure 10. Input offset voltage vs. input common mode voltage at V_{CC} = 5 V

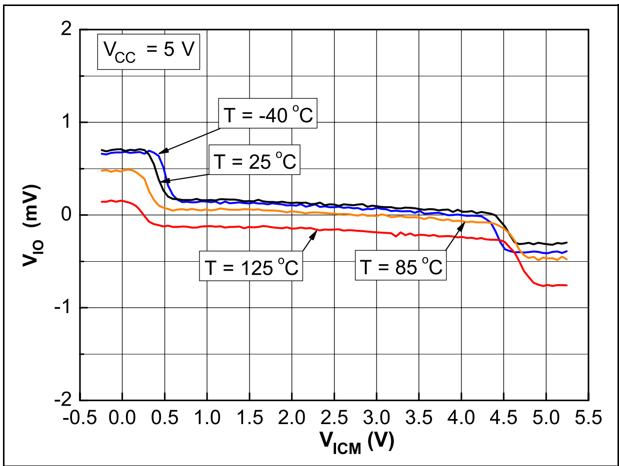


Figure 11. Input hysteresis voltage vs. input common mode voltage at V_{CC} = 5 V

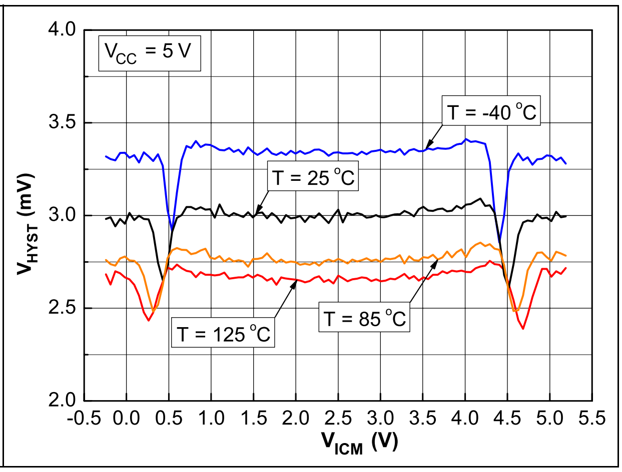


Figure 12. Input offset voltage vs. temperature

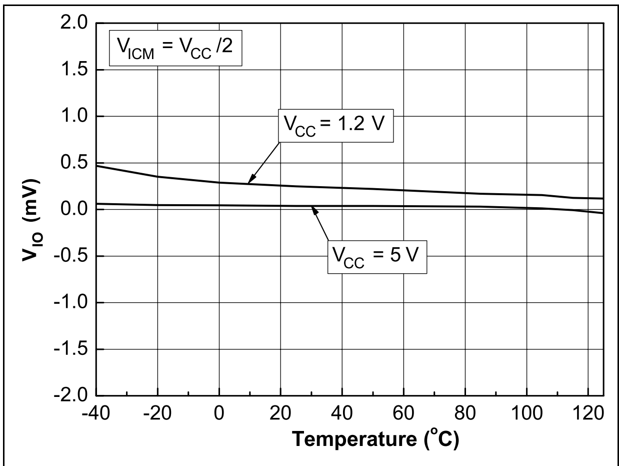


Figure 13. Input hysteresis voltage vs. temperature

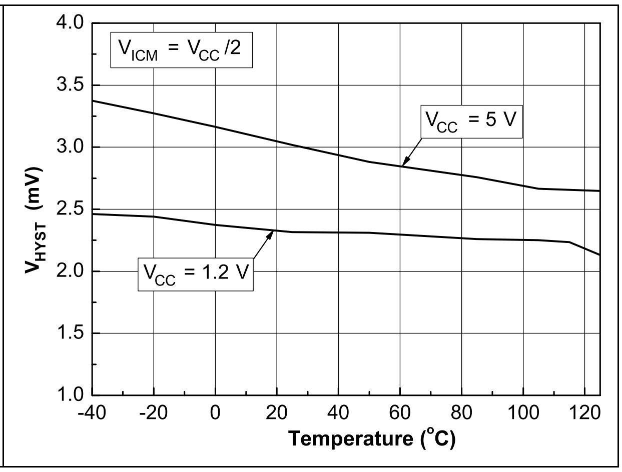


Figure 14. Output voltage drop vs. sink current at V_{CC} = 1.2 V

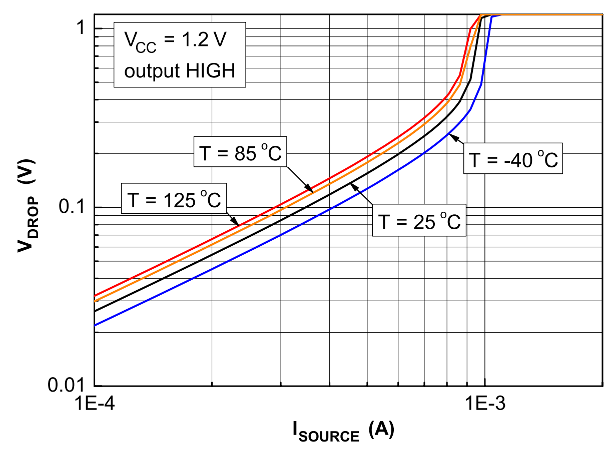


Figure 15. Output voltage drop vs. source current at V_{CC} = 1.2 V

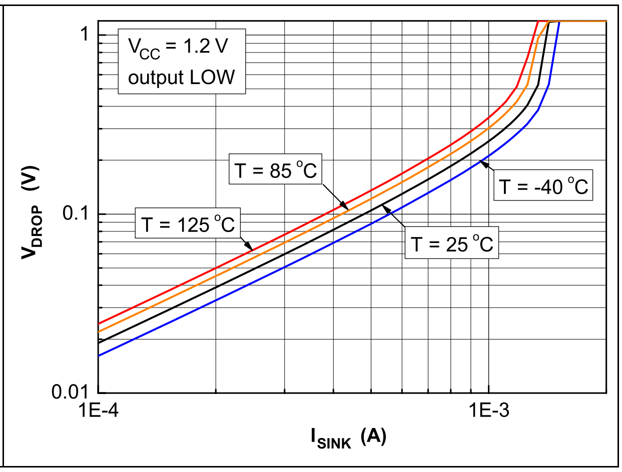


Figure 16. Output voltage drop vs. sink current at V_{CC} = 2.7 V

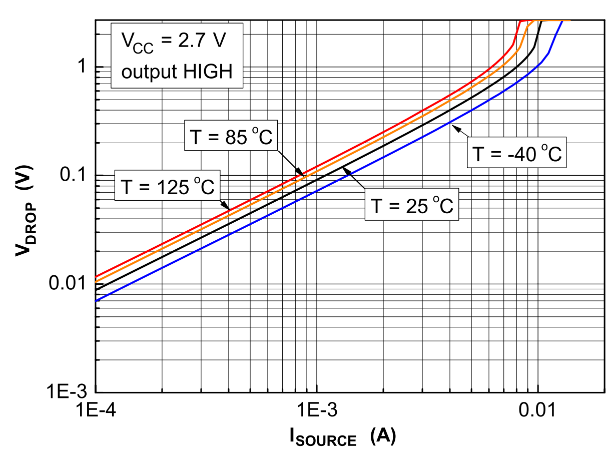


Figure 17. Output voltage drop vs. source current at V_{CC} = 2.7 V

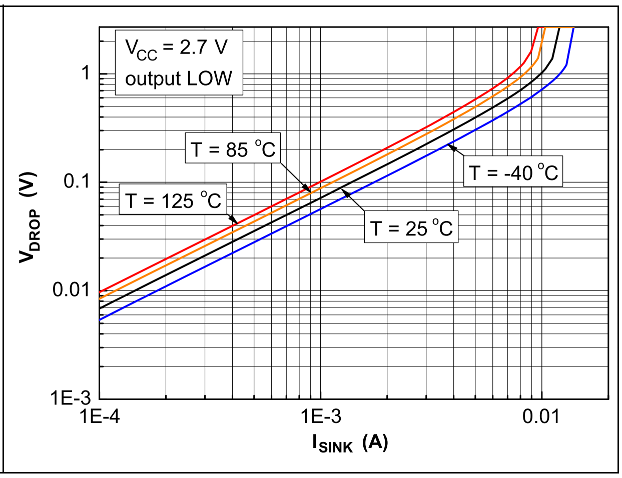


Figure 18. Output voltage drop vs. sink current at V_{CC} = 5 V

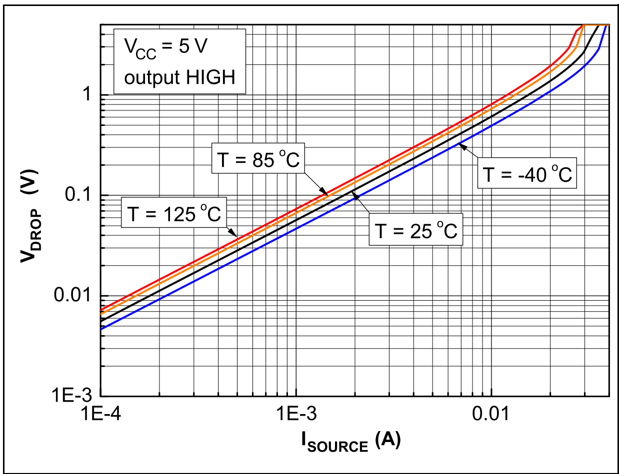


Figure 19. Output voltage drop vs. source current at V_{CC} = 5 V

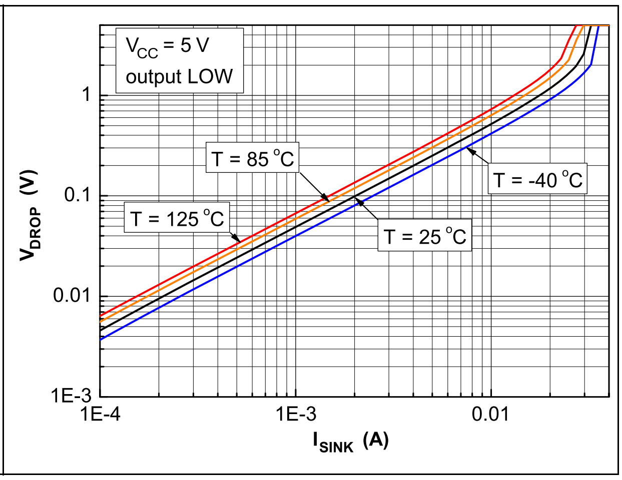


Figure 20. Propagation delay T_{PLH} vs. input common mode voltage at V_{CC} = 1.2 V

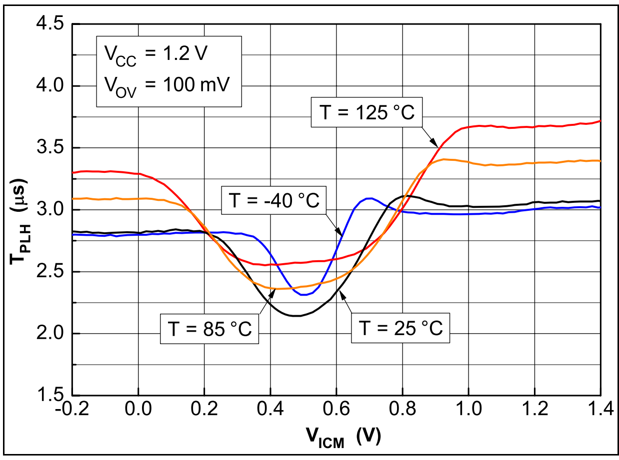


Figure 21. Propagation delay T_{PHL} vs. input common mode voltage at V_{CC} = 1.2 V

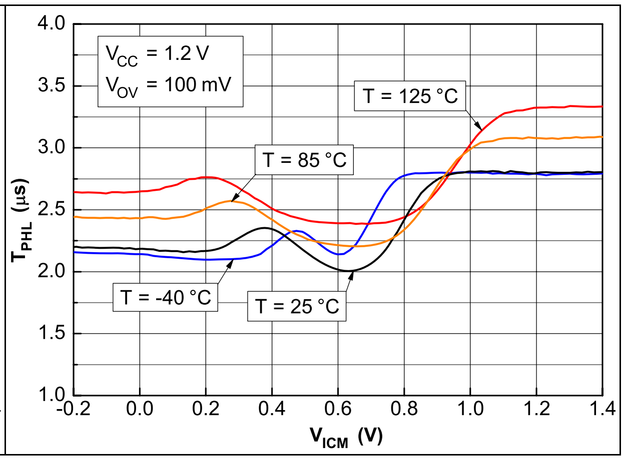


Figure 22. Propagation delay T_{PLH} vs. input common mode voltage at V_{CC} = 5 V

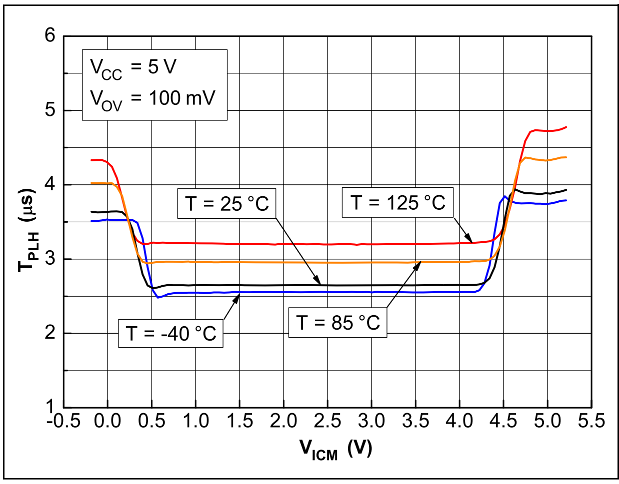


Figure 23. Propagation delay T_{PHL} vs. input common mode voltage at V_{CC} = 5 V

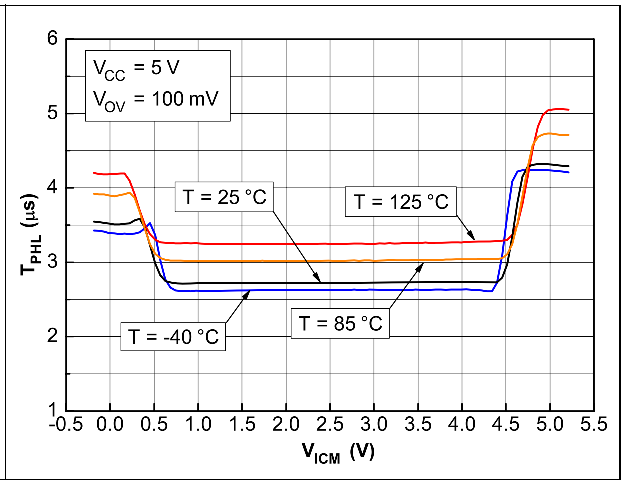


Figure 24. Propagation delay T_{PLH} vs. input signal overdrive at V_{CC} = 1.2 V

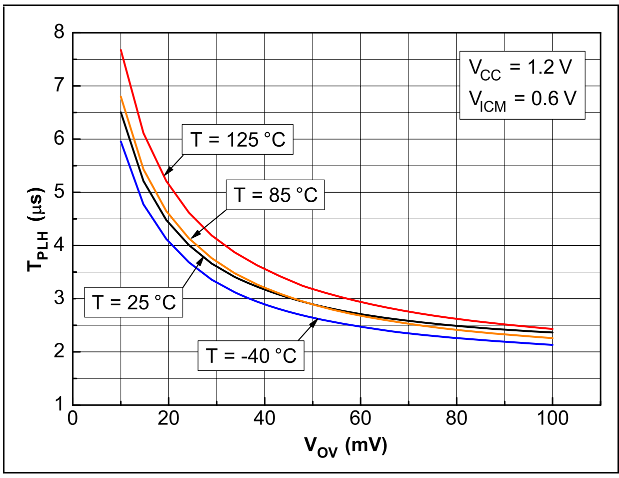


Figure 25. Propagation delay T_{PHL} vs. input signal overdrive at V_{CC} = 1.2 V

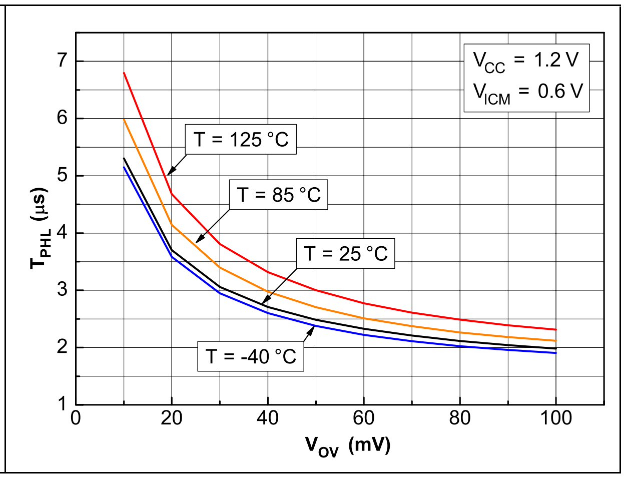


Figure 26. Propagation delay T_{PLH} vs. input signal overdrive at V_{CC} = 5 V

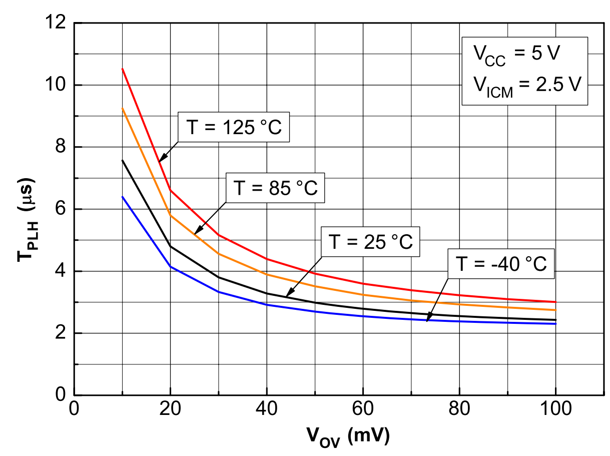


Figure 27. Propagation delay T_{PHL} vs. input signal overdrive at V_{CC} = 5 V

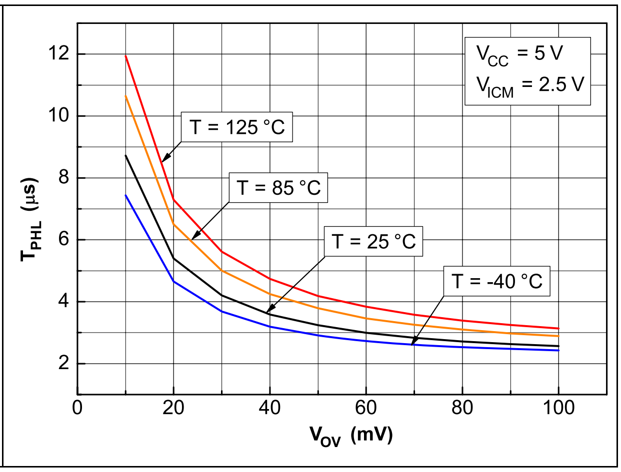


Figure 28. Propagation delay T_{PLH} vs. supply voltage for signal overdrive 10 mV

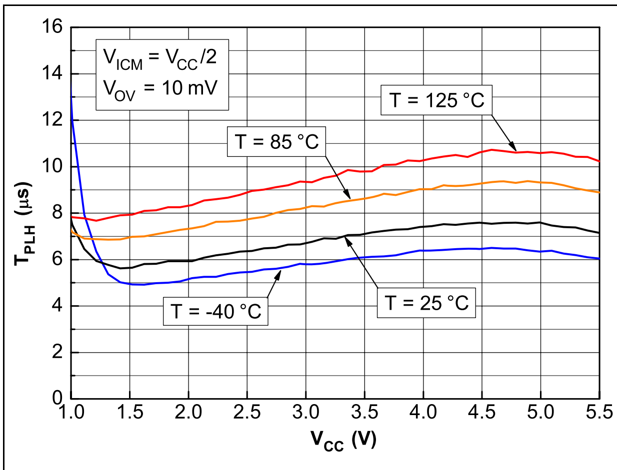


Figure 29. Propagation delay T_{PHL} vs. supply voltage for signal overdrive 10 mV

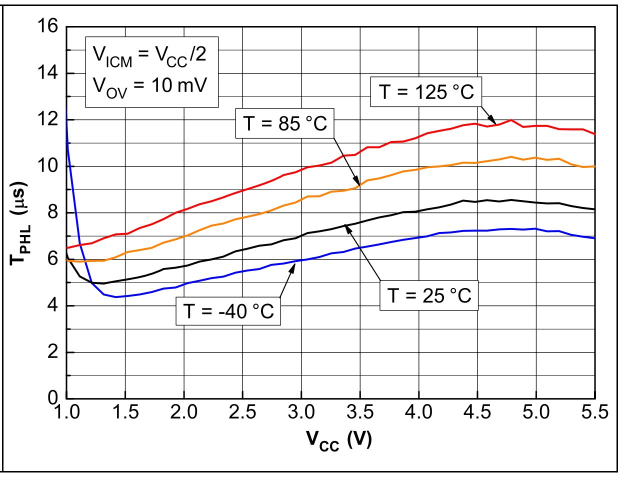


Figure 30. Propagation delay T_{PLH} vs. supply voltage for signal overdrive 100 mV

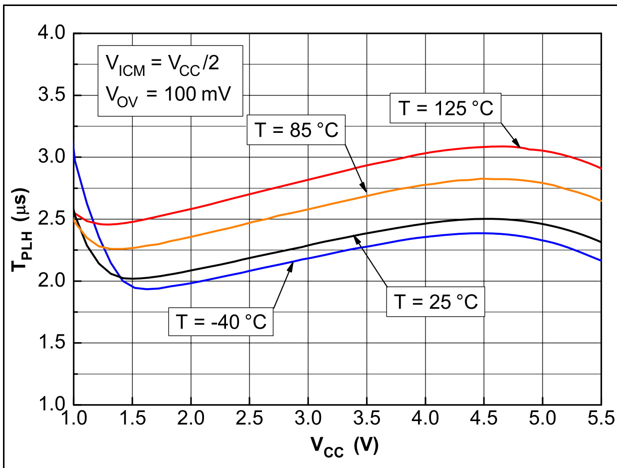


Figure 31. Propagation delay T_{PHL} vs. supply voltage for signal overdrive 100 mV

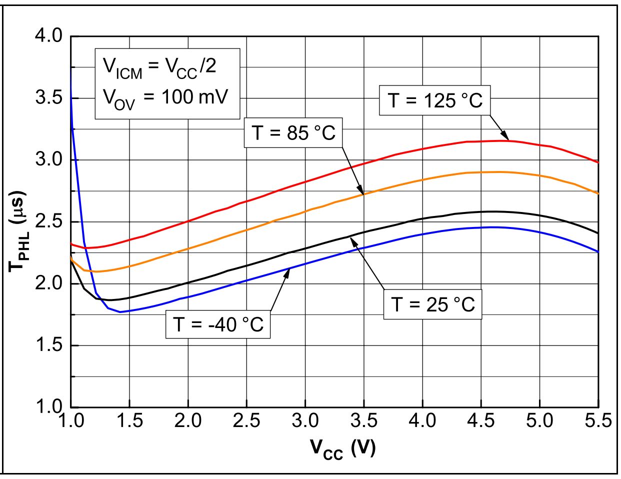


Figure 32. Propagation delay vs. temperature for signal overdrive 10 mV

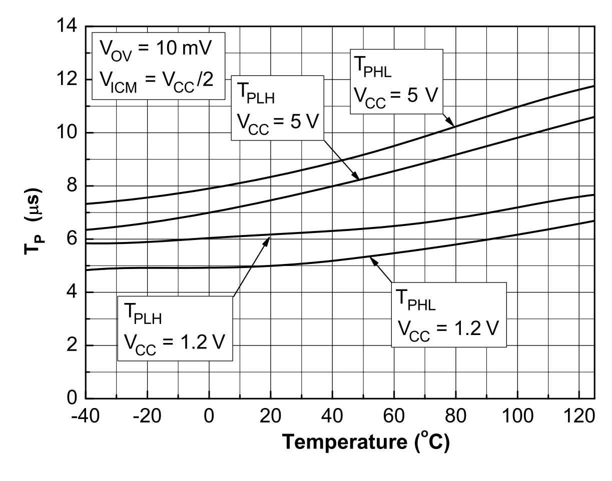
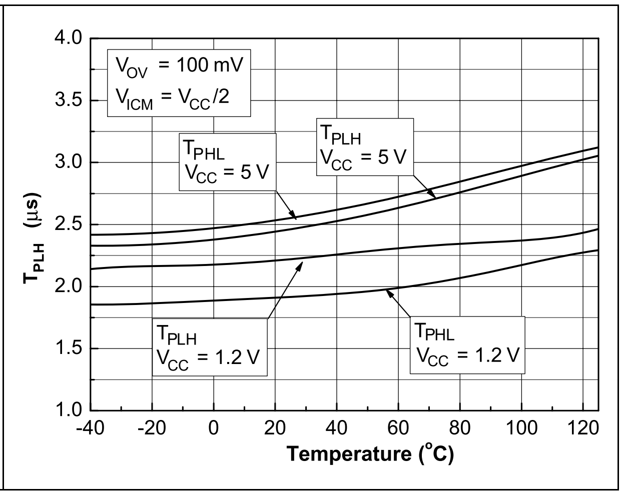


Figure 33. Propagation delay vs. temperature for signal overdrive 100 mV



3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK is an ST trademark.

3.1 SO8 package information

Figure 34. SO8 package outline

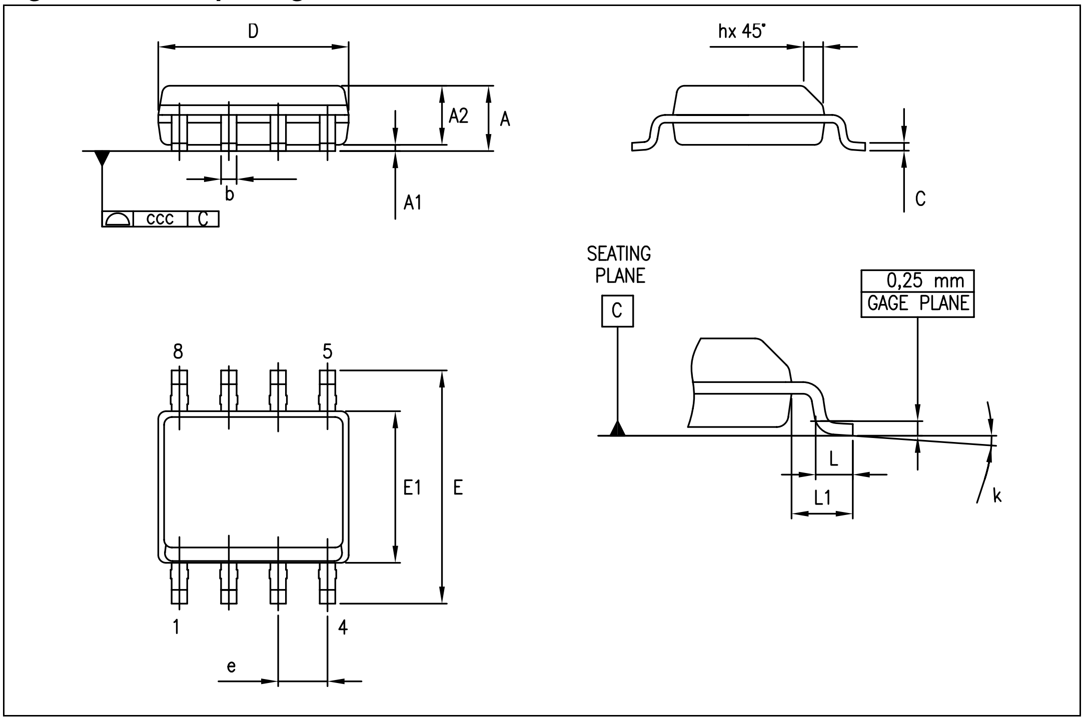


Table 6. SO8 package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
L1		1.04			0.040	
k	0°		8°	1°		8°
ccc			0.10			0.004

3.2 DFN8 2 x 2 mm package mechanical data

Figure 35. DFN8 2 x 2 mm package outline

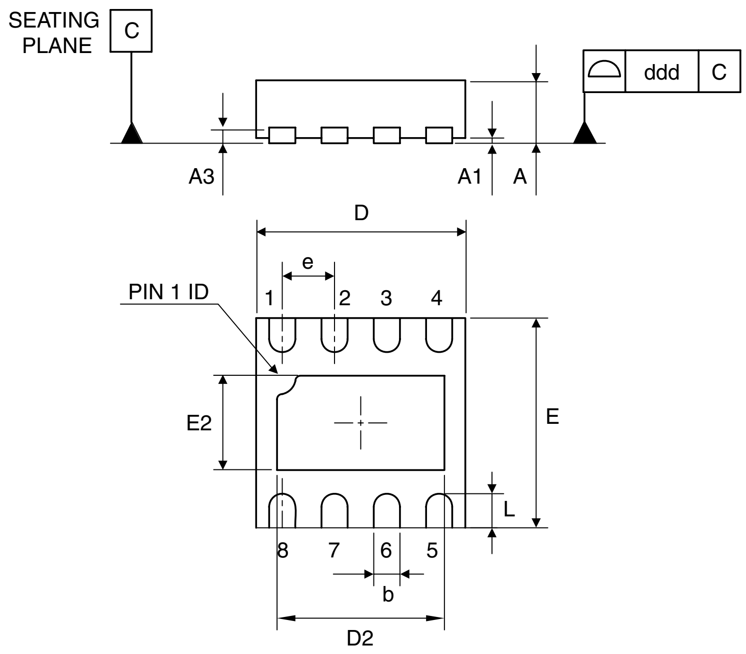
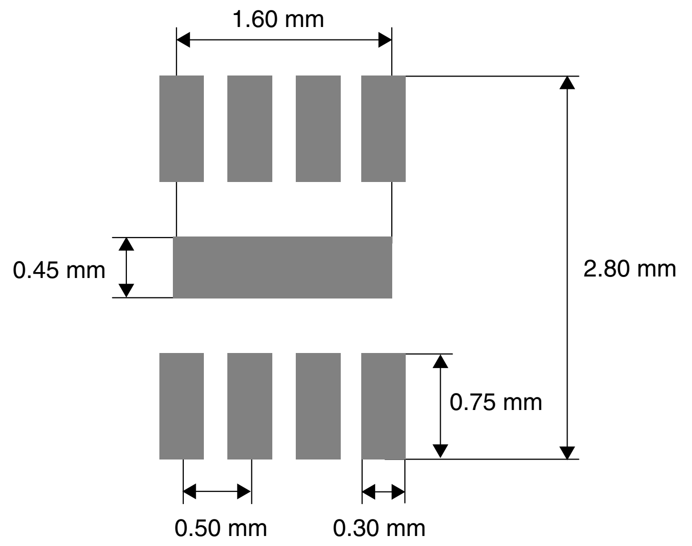


Table 7. DFN8 2 x 2 mm package mechanical data (pitch 0.5 mm)

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.51	0.55	0.60	0.020	0.022	0.024
A1			0.05			0.002
A3		0.15			0.006	
b	0.18	0.25	0.30	0.007	0.010	0.012
D	1.85	2.00	2.15	0.073	0.079	0.085
D2	1.45	1.60	1.70	0.057	0.063	0.067
E	1.85	2.00	2.15	0.073	0.079	0.085
E2	0.75	0.90	1.00	0.030	0.035	0.039
e		0.50			0.020	
L			0.50			0.020
ddd			0.08			0.003

Figure 36. DFN8 2 x 2 mm footprint recommendation



3.3 MiniSO8 package information

Figure 37. MiniSO8 package outline

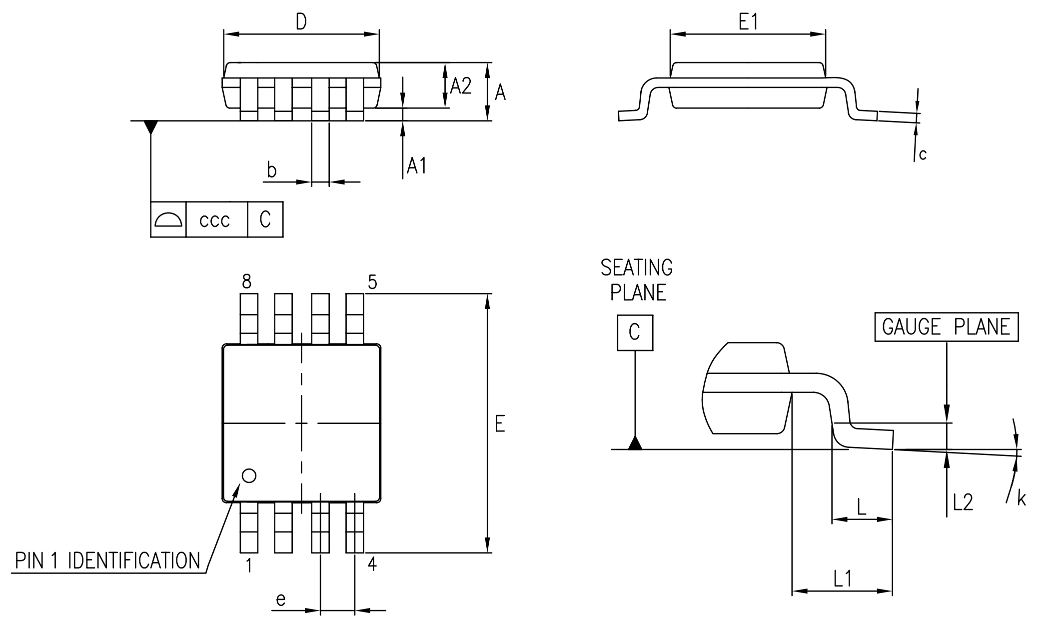


Table 8. MiniSO8 package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.10			0.043
A1	0		0.15	0		0.006
A2	0.75	0.85	0.95	0.030	0.033	0.037
b	0.22		0.40	0.009		0.016
c	0.08		0.23	0.003		0.009
D	2.80	3.00	3.20	0.11	0.118	0.126
E	4.65	4.90	5.15	0.183	0.193	0.203
E1	2.80	3.00	3.10	0.11	0.118	0.122
e		0.65			0.026	
L	0.40	0.60	0.80	0.016	0.024	0.031
L1		0.95			0.037	
L2		0.25			0.010	
k	0°		8°	0°		8°
ccc			0.10			0.004

4 Ordering information

Table 9. Order codes

Order code	Temperature range	Package	Packaging	Marking
TS882IDT	-40 to +125 °C	SO8	Tape and reel	S882I
TS882IST		MiniSO8		K514
TS882IQ2T		DFN8 2 x 2 mm		K56

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
18-Jan-2013	1	Initial release.

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